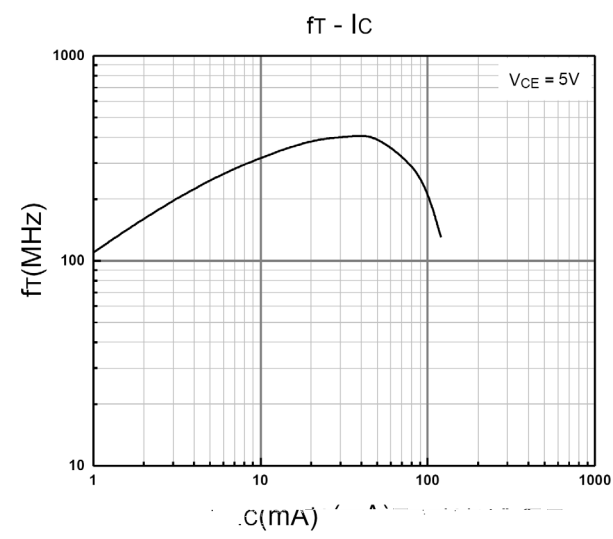
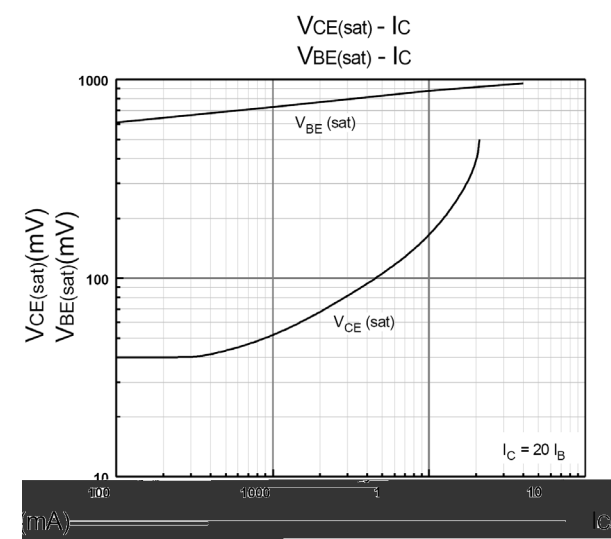
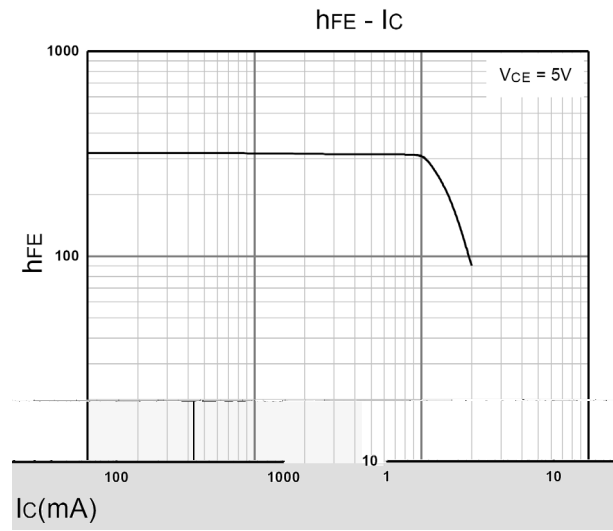
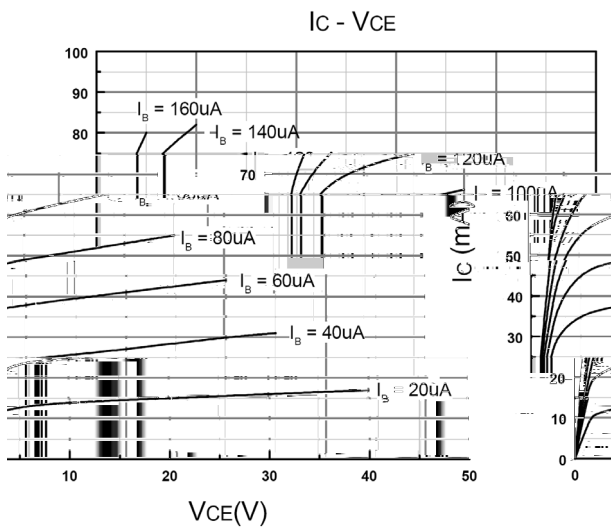


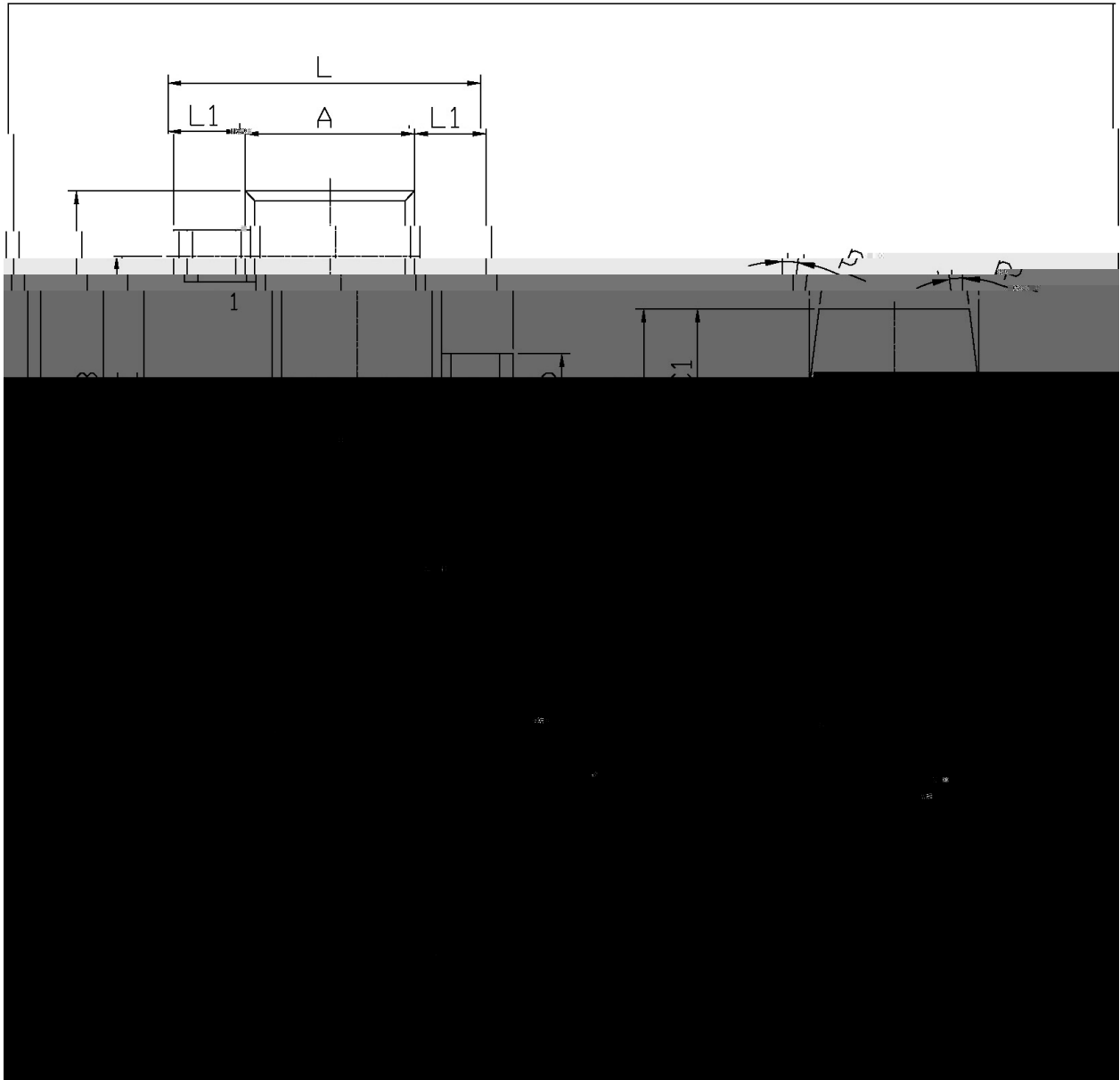
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	50	V
Collector to Emitter Voltage	V_{CEO}	45	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current	I_C	100	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

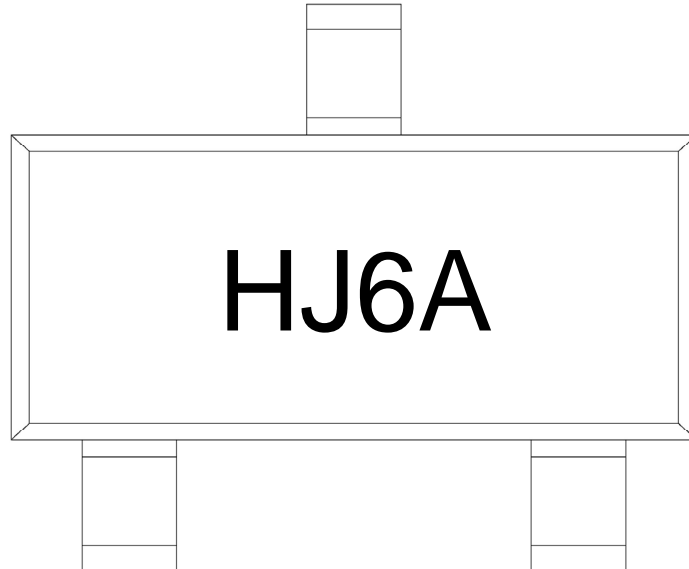
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=0.1mA$ $I_E=0$	50			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=1.0mA$ $I_B=0$	45			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=0.1mA$ $I_C=0$	5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=50V$ $I_E=0$			0.05	A
Emitter Cut-off Current	I_{EBO}	$V_{EB}=5.0V$ $I_C=0$			0.05	A
DC Current Gain	h_{FE}	$V_{CE}=5.0V$ $I_C=1.0mA$	60		1000	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=100mA$ $I_B=5.0mA$		0.14	0.3	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=100mA$ $I_B=5.0mA$		0.84	1.0	V
Base-Emitter Voltage	V_{BE}	$V_{CE}=5.0V$ $I_C=2.0mA$		0.63	0.7	V
Transition Frequency	f_T	$V_{CE}=5.0V$ $I_C=10mA$	150	270		MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=10V$ $I_E=0$ $f=1.0MHz$		2.2	3.5	pF
Noise Figure	NF	$V_{CE}=5.0V$ $I_C=0.2mA$ $R_g=2.0K$ $f=1.0KHz$ $\Delta f=200Hz$		0.9	10	dB



SOT-23

单位: mm





H

J6

A hFE

Note:

H Company Code

J6 Product Type Code

A hFE Classifications Symbol Code

Temperature Profile for IR Reflow Soldering(Pb-Free)

Note:

- | | | | |
|---|-----------|-------------|---|
| 1 | 150 ~ 180 | 60 ~ 90sec; | 1.Preheating:150~180 , Time:60~90sec. |
| 2 | 245±5 | 5±0.5sec; | 2.Peak Temp.:245±5 , Duration:5±0.5sec. |
| 3 | 2 ~ 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

260±5	10±1 sec.	Temp.:260±5	Time:10±1 sec
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/ REEL